

**3DD264(266), 3DD267(269)****NPN Silicon Low Frequency High Power Transistor****Features:**

1. Using triple-diffusion process.Excellent capacity in anti-burnout.Excellent second breakdown capacity.
2. Good temperature stability.Excellent thermal fatigue capability.
3. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
4. Use for Low-speed switch,low frequency power amplify,power adjustment.
5. Quality Class: JP, JT, JCT, GS, G, G+

**TECHNICAL DATA:****(Ta = 25°C )**

Parameter name	Symbols	Unit	Specifications				
			3DD264			3DD267	
			A	B	C	D	E
Collector-Emitter Voltage	$V_{CEO}$	V	300	400	500	600	700
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	300	400	500	600	700
Emitter-Base Voltage	$V_{EBO}$	V	5			5	
Max. Collector Current	$I_{CM}$	A	7			7	
Max. Collector Dissipation	$P_{CM}$	W	100 ( $T_c \leq 75^\circ C$ )			150 ( $T_c \leq 75^\circ C$ )	
Junction Temperature	$T_{jm}$	$^\circ C$	175				
Storage Temperature	$T_{stg}$	$^\circ C$	-55~+175				
Collector-Emitter Leakage Current	$I_{CEO}$	mA	2.0 ( $V_{CE}=100V$ )				
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	1.8 ( $I_c=3.5A, I_B=0.7A$ )			1.8 ( $I_c=5A, I_B=1A$ )	
DC Current Gain	$h_{FE}$		Max.:180,Min.:7 ( $V_{CE}=10V, I_c=3.5A$ )			Max.:180, Min.:7 ( $V_{CE}=10V, I_c=5A$ )	
E-Base Breakdown Voltage	$V_{(BR)EBO}$	V	$\geq 5$ ( $I_E=2mA$ )			$\geq 5$ ( $I_E=2mA$ )	

**hFE Colored:**

Color	Brown	Red	Orange	Yellow	Green	Blue	Purple
$h_{FE}$	7~15	15~25	25~40	40~55	55~80	80~120	120~180

**Outline and Dimensions:**